

General Purpose Transistors NPN Silicon

- Moisture Sensitivity Level: 1
- ESD Rating Human Body Model: >4000 V
 - Machine Model: >400 V
- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

MAXIMUM RATINGS

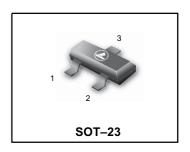
Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO		Vdc
LBC846		65	
LBC847, LBC850		45	
LBC848, LBC849		30	
Collector-Base Voltage	V _{CBO}		Vdc
LBC846		80	
LBC847, LBC850		50	
LBC848, LBC849		30	
Emitter-Base Voltage	V _{EBO}		Vdc
LBC846		6.0	
LBC847, LBC850		6.0	
LBC848, LBC849		5.0	
Collector Current – Continuous	IC	100	mAdc

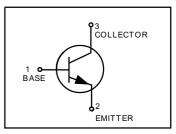
THERMAL CHARACTERISTICS

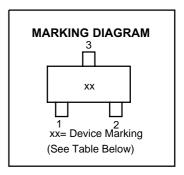
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1.) T _A = 25°C	P _D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction to Ambient (Note 1.)	$R_{ heta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2.) T _A = 25°C Derate above 25°C	PD	300	mW mW/°C
			,
Thermal Resistance, Junction to Ambient (Note 2.)	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	–55 to +150	°C

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

LBC846ALT1G S-LBC846ALT1G Series









DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Package	Shipping
LBC846ALT1G S-LBC846ALT1G	1A	SOT-23	3000/Tape&Reel
LBC846ALT3G S-LBC846ALT3G	1A	SOT-23	10000/Tape&Reel
LBC846BLT1G S-LBC846BLT1G	1B	SOT-23	3000/Tape&Reel
LBC846BLT3G S-LBC846BLT3G	1B	SOT-23	10000/Tape&Reel
LBC847ALT1G S-LBC847ALT1G	1E	SOT-23	3000/Tape&Reel
LBC847ALT3G S-LBC847ALT3G	1E	SOT-23	10000/Tape&Reel
LBC847BLT1G S-LBC847BLT1G	1F	SOT-23	3000/Tape&Reel
LBC847BLT3G S-LBC847BLT3G	1F	SOT-23	10000/Tape&Reel
LBC847CLT1G S-LBC847CLT1G	1G	SOT-23	3000/Tape&Reel
LBC847CLT3G S-LBC847CLT3G	1G	SOT-23	10000/Tape&Reel
LBC848ALT1G S-LBC848ALT1G	1J	SOT-23	3000/Tape&Reel
LBC848ALT3G S-LBC848ALT3G	1J	SOT-23	10000/Tape&Reel
LBC848BLT1G S-LBC848BLT1G	1K	SOT-23	3000/Tape&Reel
LBC848BLT3G S-LBC848BLT3G	1K	SOT-23	10000/Tape&Reel
LBC848CLT1G S-LBC848CLT1G	1L	SOT-23	3000/Tape&Reel
LBC848CLT3G S-LBC848CLT3G	1L	SOT-23	10000/Tape&Reel
LBC849BLT1G S-LBC849BLT1G	2B	SOT-23	3000/Tape&Reel
LBC849BLT3G S-LBC849BLT3G	2B	SOT-23	10000/Tape&Reel
LBC849CLT1G S-LBC849CLT1G	2C	SOT-23	3000/Tape&Reel
LBC849CLT3G S-LBC849CLT3G	2C	SOT-23	10000/Tape&Reel
LBC850BLT1G S-LBC850BLT1G	2E	SOT-23	3000/Tape&Reel
LBC850BLT3G S-LBC850BLT3G	2E	SOT-23	10000/Tape&Reel
LBC850CLT1G S-LBC850CLT1G	2G	SOT-23	3000/Tape&Reel
LBC850CLT3G S-LBC850CLT3G	2G	SOT-23	10000/Tape&Reel



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

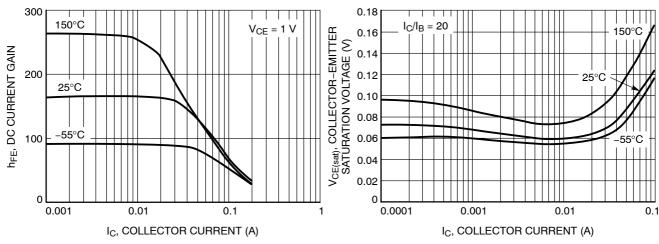
Characteristic			Min	Тур	Max	Unit
OFF CHARACTERISTICS				•	•	
Collector–Emitter Breakdown Voltage (I _C = 10 mA)	LBC846A,B LBC847A,B,C, LBC850B,C LBC848A,B,C, LBC849B,C	V(BR)CEO	65 45 30	_ _ _	- - -	V
Collector–Emitter Breakdown Voltage (I _C = 10 μ A, V _{EB} = 0)	LBC846A,B LBC847A,B,C, LBC850B,C LBC848A,B,C, LBC849B,C	V(BR)CES	80 50 30	- - -	- - -	V
Collector–Base Breakdown Voltage ($I_C = 10 \mu A$)	LBC846A,B LBC847A,B,C, LBC850B,C LBC848A,B,C, LBC849B,C	V(BR)CBO	80 50 30	- - -	- - -	V
Emitter–Base Breakdown Voltage (I _E = 1.0 μA)	LBC846A,B LBC847A,B,C, LBC850B,C LBC848A,B,C, LBC849B,C	V _{(BR)EBO}	6.0 6.0 5.0	_ _ _	- - -	V
Collector Cutoff Current (V _{CB} = 30 V)	(V _{CB} = 30 V, T _A = 150°C)	ICBO	-	_ _	15 5.0	nA μA
ON CHARACTERISTICS		•		•	•	•
DC Current Gain		hFE				_
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	LBC846A, LBC847A, LBC848A LBC846B, LBC847B, LBC848B, LBC849B, LBC850B C, LBC848C, LBC849C, LBC850C		110 200 420	180 290 520	220 450 800	
Collector–Emitter Saturation Voltage ($I_C = 10 \text{ mA}$, $I_B = 0.5 \text{ mA}$) ($I_C = 100 \text{ mA}$, $I_B = 5.0 \text{ mA}$)		VCE(sat)	-	_ _	0.25 0.6	V
Base–Emitter Saturation Voltage ($I_C = 10 \text{ mA}$, $I_B = 0.5 \text{ mA}$) ($I_C = 100 \text{ mA}$, $I_B = 5.0 \text{ mA}$)		V _{BE(sat)}	-	0.7 0.9	_ _	V
Base–Emitter Voltage (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 10 mA, V_{CE} = 5.0 V)		VBE(on)	580 -	660 -	700 770	mV
SMALL-SIGNAL CHARACTERIS	TICS					
Current–Gain – Bandwidth Product ($I_C = 10 \text{ mA}$, $V_{CE} = 5.0 \text{ Vdc}$, $f = 100 \text{ MHz}$)		fΤ	100	_	_	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)		C _{obo}	-	-	4.5	pF
Noise Figure (I_C = 0.2 mA, (V_{CE} = 5.0 Vdc, R_S = 2.0 k Ω LBC846A,B, LBC847A,B,C, LBC848A,B,C f = 1.0 kHz, BW = 200 Hz) LBC849B,C, LBC850B,C		NF	_ _	_ _	10 4.0	dB



1.0

LBC846ALT1G Series S-LBC846ALT1G Series

LBC846A, LBC847A, LBC848A



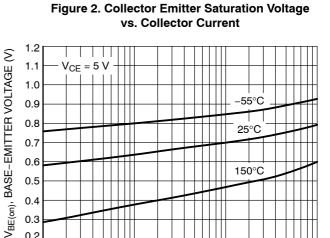
0.4

0.3

0.2

0.0001

Figure 1. DC Current Gain vs. Collector Current



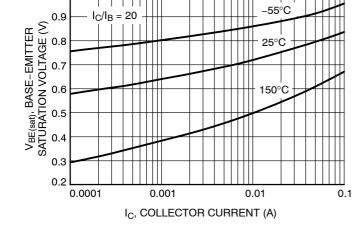


Figure 3. Base Emitter Saturation Voltage vs. **Collector Current**

I_C, COLLECTOR CURRENT (A) Figure 4. Base Emitter Voltage vs. Collector Current

0.01

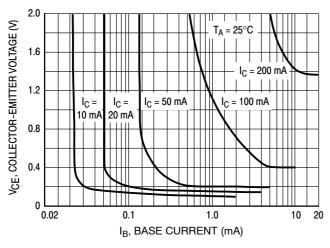
0.1

0.001



LBC846A, LBC847A, LBC848A

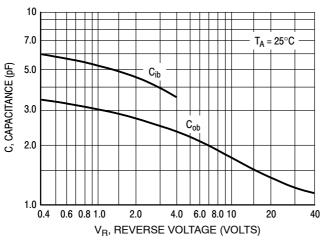
400



TEMPERATURE COEFFICIENT (mV/°C) -55°C to +125°C 1.2 1.6 2.0 2.4 2.8 θ⁄B, 0.2 1.0 10 100 I_C, COLLECTOR CURRENT (mA)

Figure 5. Collector Saturation Region

Figure 6. Base-Emitter Temperature Coefficient



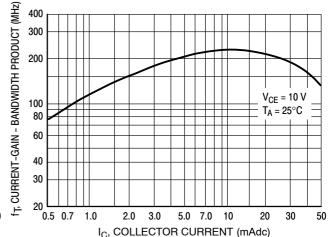


Figure 7. Capacitances

Figure 8. Current-Gain - Bandwidth Product



LBC846B

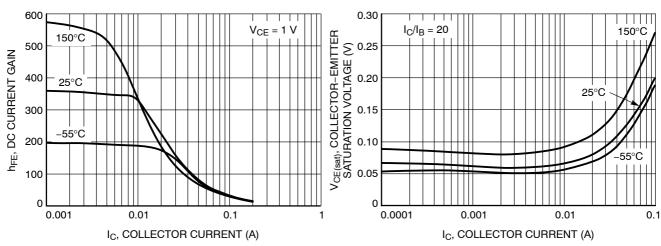


Figure 9. DC Current Gain vs. Collector Current

Figure 10. Collector Emitter Saturation Voltage vs. Collector Current

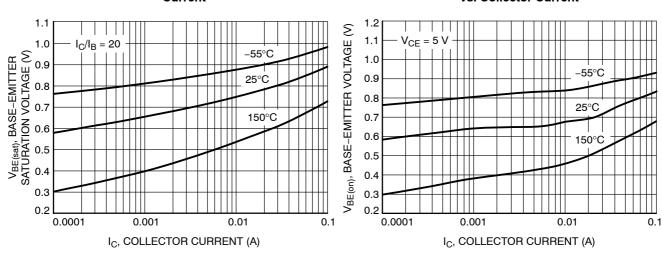
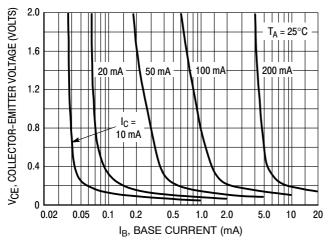


Figure 11. Base Emitter Saturation Voltage vs.
Collector Current

Figure 12. Base Emitter Voltage vs. Collector Current



LBC846B



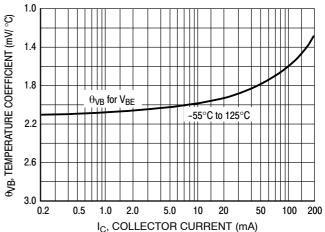


Figure 13. Collector Saturation Region

Figure 14. Base-Emitter Temperature Coefficient

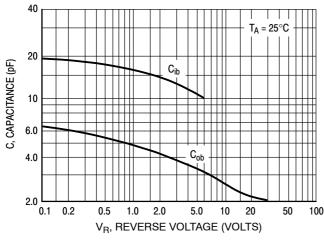


Figure 15. Capacitance

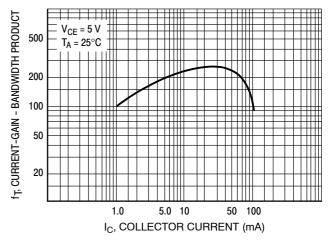


Figure 16. Current-Gain - Bandwidth Product



LBC847B, LBC848B, LBC849B, LBC850B

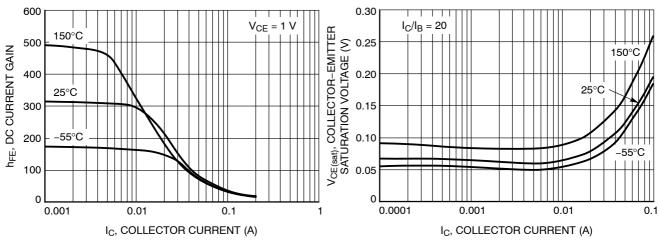


Figure 17. DC Current Gain vs. Collector Current

Figure 18. Collector Emitter Saturation Voltage vs. Collector Current

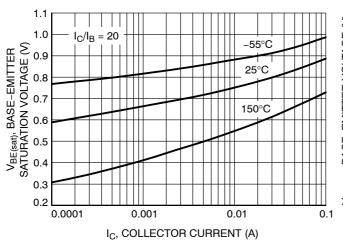


Figure 19. Base Emitter Saturation Voltage vs.
Collector Current

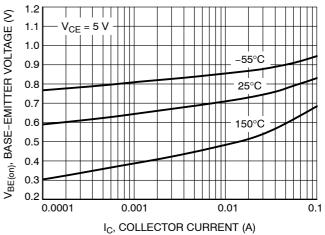


Figure 20. Base Emitter Voltage vs. Collector Current



LBC847B, LBC848B, LBC849B, LBC850B

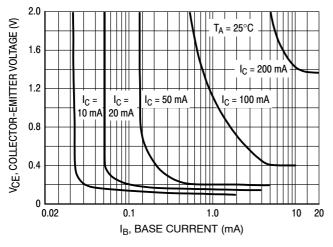
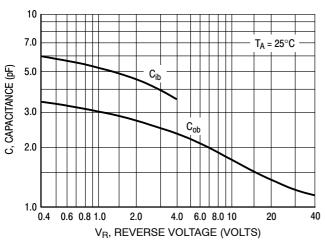


Figure 21. Collector Saturation Region

Figure 22. Base-Emitter Temperature Coefficient



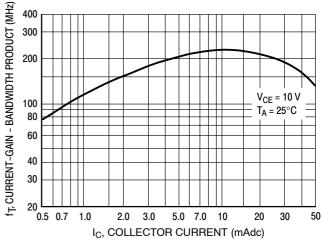


Figure 23. Capacitances

Figure 24. Current-Gain - Bandwidth Product



LBC847C, LBC848C, LBC849C, LBC850C

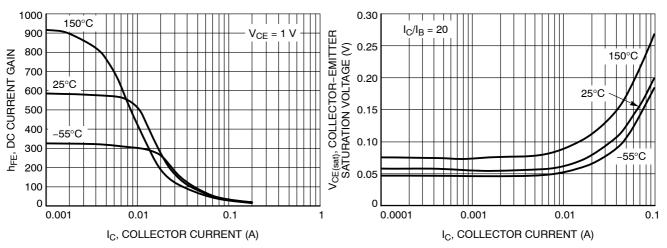


Figure 25. DC Current Gain vs. Collector Current

Figure 26. Collector Emitter Saturation Voltage vs. Collector Current

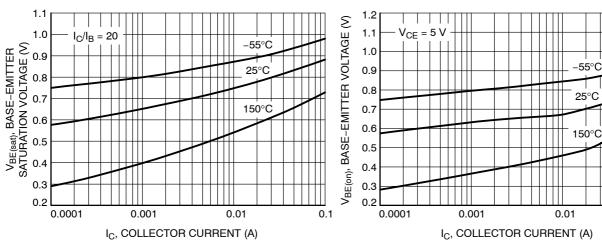


Figure 27. Base Emitter Saturation Voltage vs.
Collector Current

Figure 28. Base Emitter Voltage vs. Collector Current

0.1



LBC847C, LBC848C, LBC849C, LBC850C

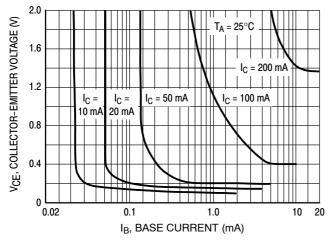


Figure 29. Collector Saturation Region

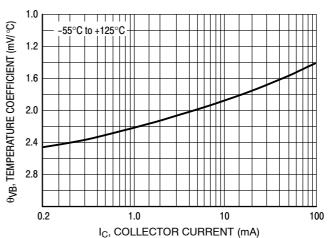


Figure 30. Base–Emitter Temperature Coefficient

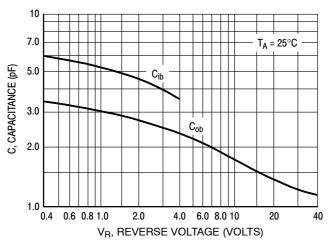


Figure 31. Capacitances

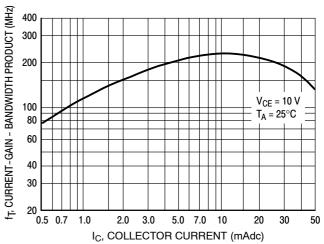


Figure 32. Current-Gain - Bandwidth Product



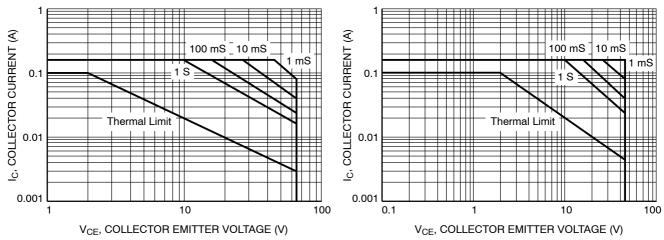


Figure 33. Safe Operating Area for LBC846A, LBC846B

Figure 34. Safe Operating Area for LBC847A, LBC847B, LBC847C, LBC850B, LBC850C

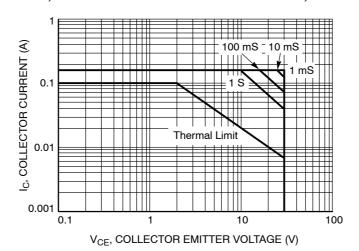
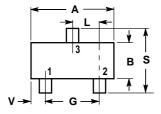
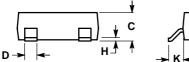


Figure 35. Safe Operating Area for LBC848A, LBC848B, LBC848C, LBC849B, LBC849C



SOT-23







NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS		
Dilvi	MIN	MAX	MIN	MAX	
Α	0.1102	0.1197	2.80	3.04	
В	0.0472	0.0551	1.20	1.40	
С	0.0350	0.0440	0.89	1.11	
D	0.0150	0.0200	0.37	0.50	
G	0.0701	0.0807	1.78	2.04	
Н	0.0005	0.0040	0.013	0.100	
J	0.0034	0.0070	0.085	0.177	
K	0.0140	0.0285	0.35	0.69	
L	0.0350	0.0401	0.89	1.02	
S	0.0830	0.1039	2.10	2.64	
V	0.0177	0.0236	0.45	0.60	

